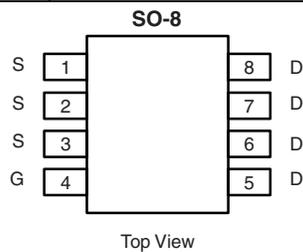


## N-Channel 30-V (D-S) MOSFET with Schottky Diode

MOSFET PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
30	0.016 at V <sub>GS</sub> = 10 V	9.5
	0.021 at V <sub>GS</sub> = 4.5 V	7.7

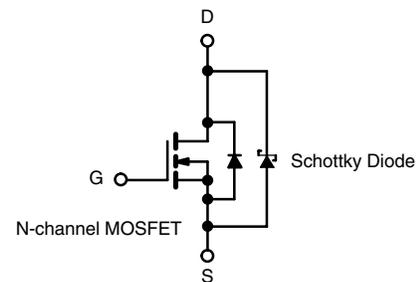
SCHOTTKY PRODUCT SUMMARY		
V <sub>DS</sub> (V)	V <sub>SD</sub> (V) Diode Forward Voltage	I <sub>F</sub> (A)
30	0.50 V at 1.0 A	1.4



Ordering Information: Si4812BDY-T1-E3 (Lead (Pb)-free)  
Si4812BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- LITTLE FOOT® Plus Power MOSFET
- 100 % R<sub>g</sub> Tested



ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted					
Parameter	Symbol	Limit		Unit	
		10 s	Steady State		
Drain-Source Voltage (MOSFET)	V <sub>DS</sub>	30		V	
Reverse Voltage (Schottky)		30			
Gate-Source Voltage (MOSFET)	V <sub>GS</sub>	± 20			
Continuous Drain Current (T <sub>J</sub> = 150 °C) (MOSFET) <sup>a, b</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	9.5	7.3	A
		T <sub>A</sub> = 70 °C	7.7	5.9	
Pulsed Drain Current (MOSFET)	I <sub>DM</sub>	50			
Continuous Source Current (MOSFET Diode Conduction) <sup>a, b</sup>	I <sub>S</sub>	2.1	1.2	A	
Average Forward Current (Schottky)	I <sub>F</sub>	1.4	0.8		
Pulsed Forward Current (Schottky)	I <sub>FM</sub>	30			
Single Pulse Avalanche Current	I <sub>AS</sub>	5		mJ	
Avalanche Energy		E <sub>AS</sub>	1.25		
Maximum Power Dissipation (MOSFET) <sup>a, b</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	2.5	1.4	W
		T <sub>A</sub> = 70 °C	1.6	0.9	
Maximum Power Dissipation (Schottky) <sup>a, b</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	2.0	1.2	
		T <sub>A</sub> = 70 °C	1.3	0.8	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Device	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (t ≤ 10 s) <sup>a</sup>	MOSFET	R <sub>thJA</sub>	40	50	°C/W
	Schottky		50	60	
Maximum Junction-to-Ambient (t = Steady State) <sup>a</sup>	MOSFET		72	90	
	Schottky		85	100	
Maximum Junction-to-Foot (t = Steady State) <sup>a</sup>	MOSFET	R <sub>thJF</sub>	18	23	
	Schottky	R <sub>thJF</sub>	24	30	

Notes:

a. Surface Mounted on FR4 board.

b. t ≤ 10 s.

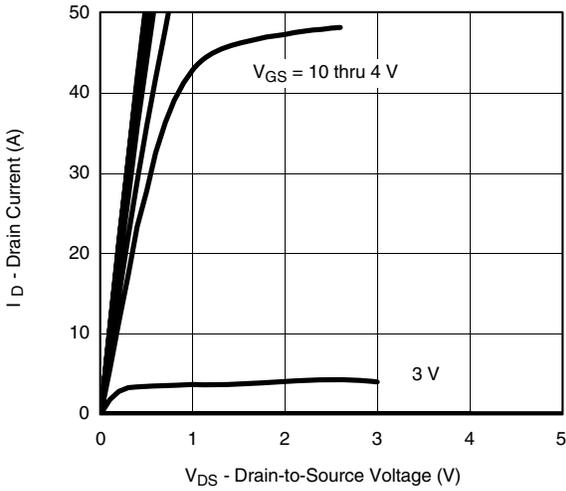
<b>MOSFET AND SCHOTTKY SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current (MOSFET and Schottky)	$I_{DSS}$	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$		0.004	0.100	mA
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$		0.7	10	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		3.0	20	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 9.5\text{ A}$		0.013	0.016	$\Omega$
		$V_{GS} = 4.5\text{ V}, I_D = 7.7\text{ A}$		0.0165	0.021	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 9.5\text{ A}$		45		S
Schottky Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.0\text{ A}, V_{GS} = 0\text{ V}$		0.45	0.50	V
		$I_S = 1.0\text{ A}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		0.33	0.42	
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 9.5\text{ A}$		8.5	13	nC
Gate-Source Charge	$Q_{gs}$			3		
Gate-Drain Charge	$Q_{gd}$			2.6		
Gate Resistance	$R_g$		0.3	0.7	1.1	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		15	25	ns
Rise Time	$t_r$			13	20	
Turn-Off Delay Time	$t_{d(off)}$			20	30	
Fall Time	$t_f$			8	15	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		22	35	

## Notes:

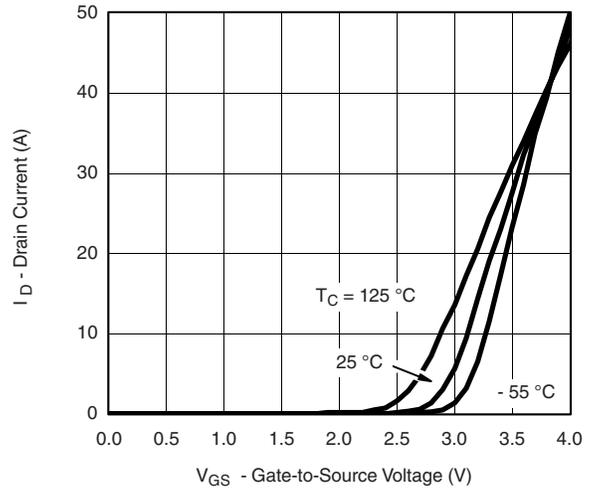
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

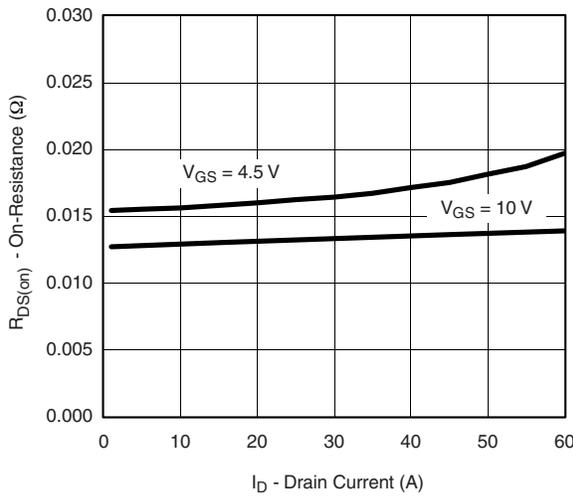
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



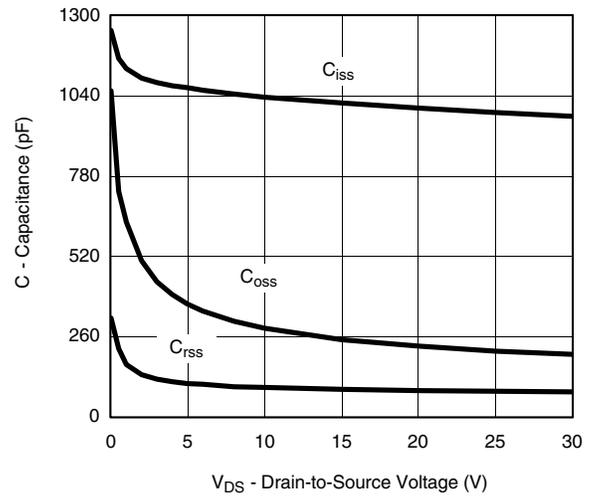
**Output Characteristics**



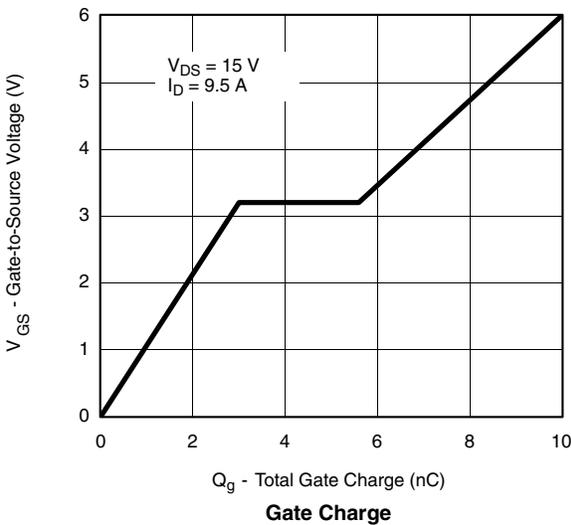
**Transfer Characteristics**



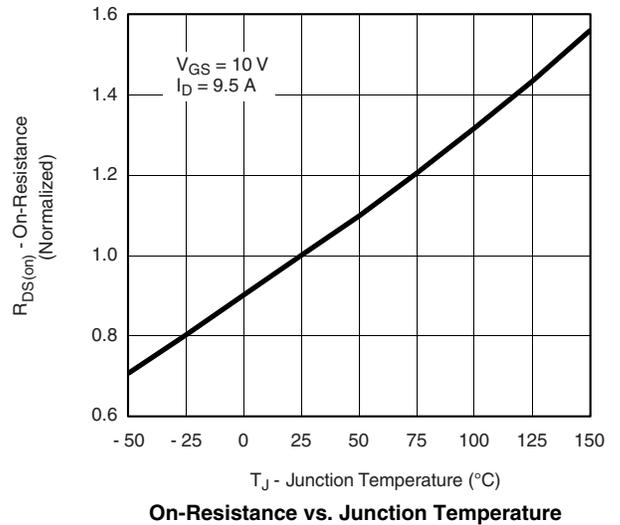
**On-Resistance vs. Drain Current**



**Capacitance**

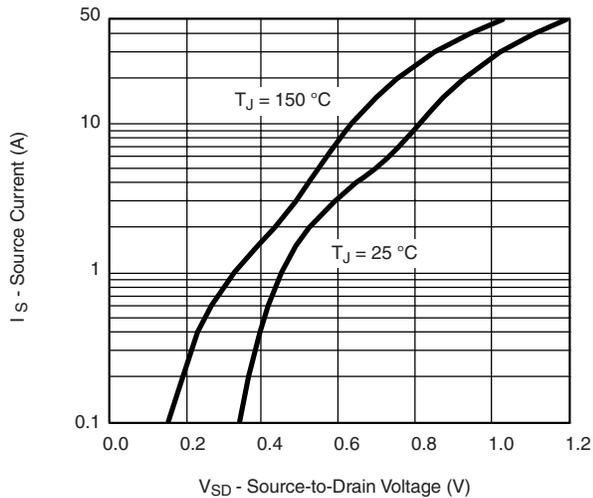


**Gate Charge**

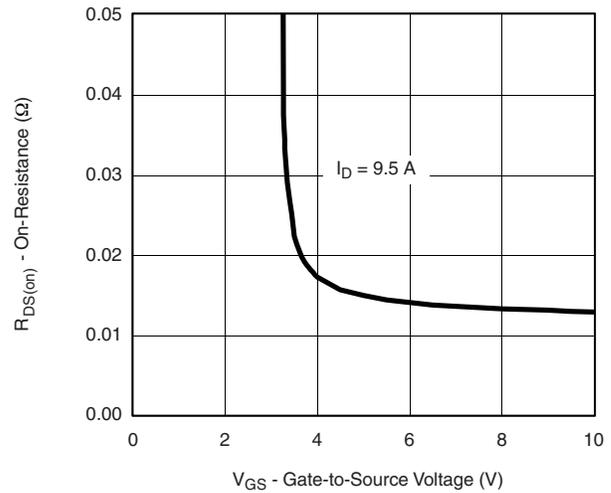


**On-Resistance vs. Junction Temperature**

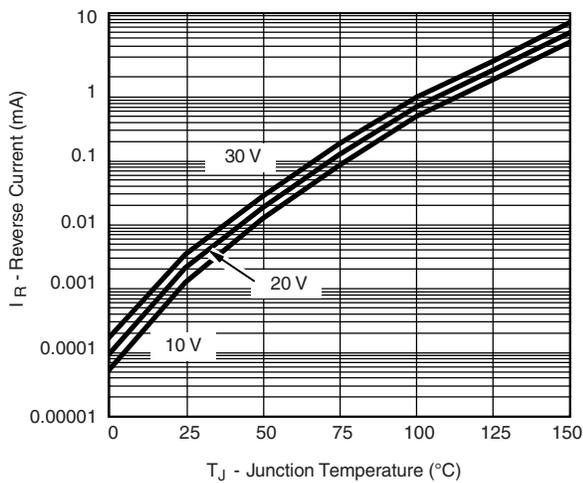
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



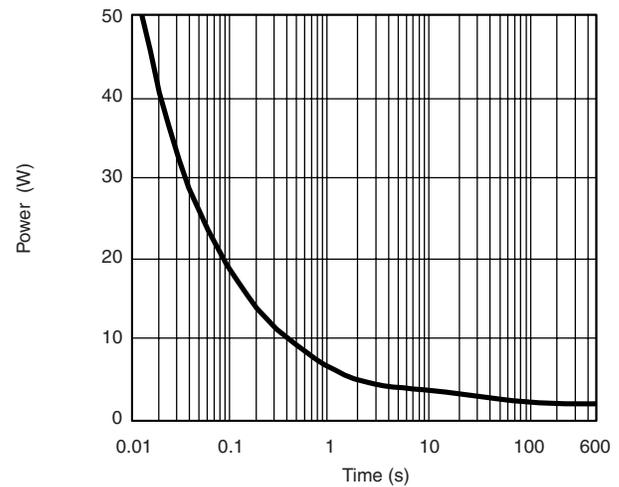
**Source-Drain Diode Forward Voltage**



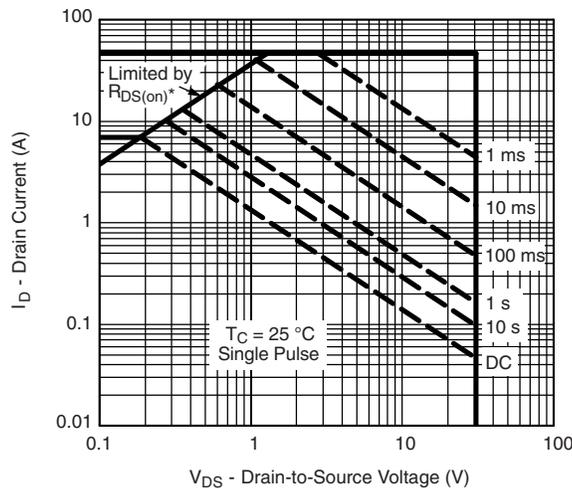
**On-Resistance vs. Gate-to-Source Voltage**



**Reverse Current (Schottky)**



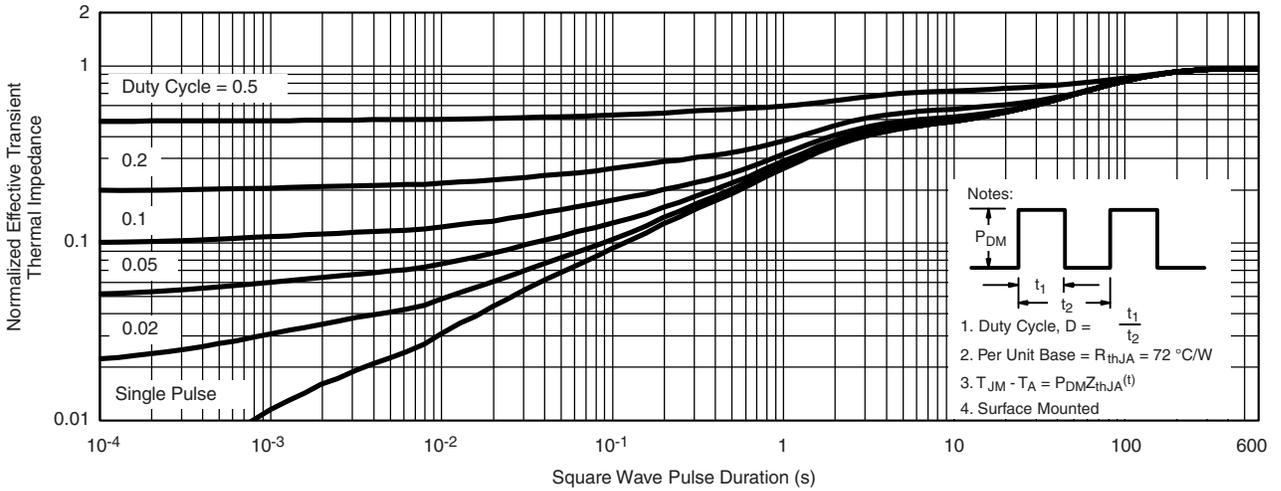
**Single Pulse Power (MOSFET)**



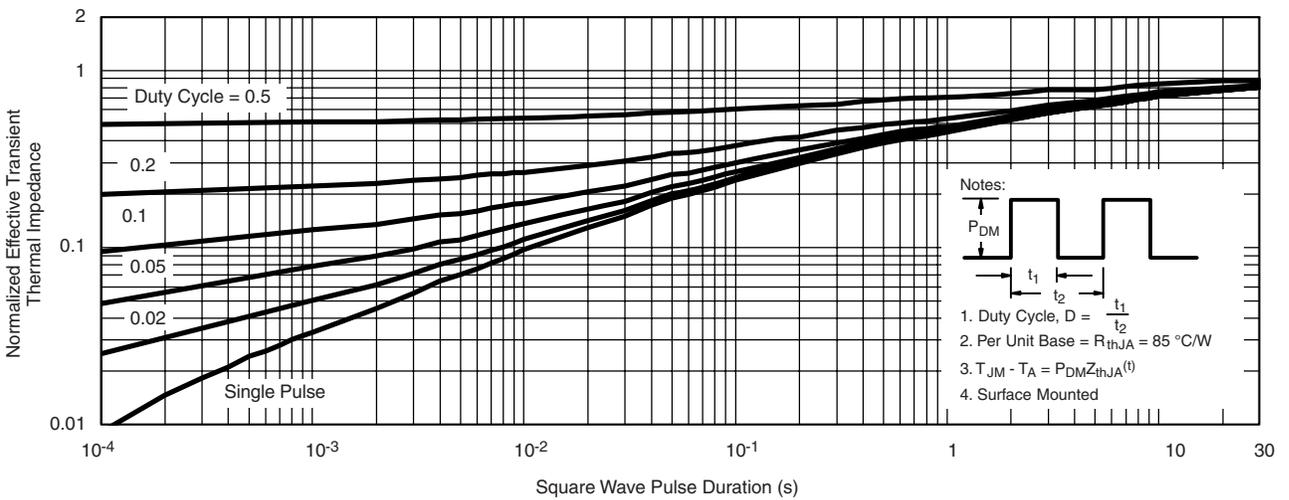
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**Safe Operating Area, Junction-to-Case**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Normalized Thermal Transient Impedance, Junction-to-Ambient (MOSFET)**

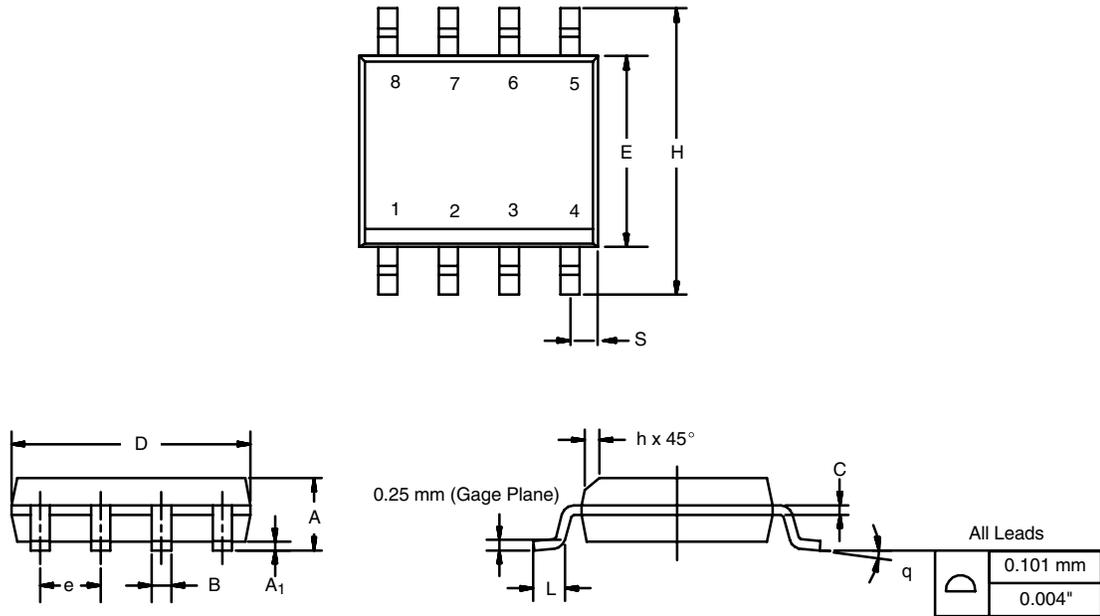


**Normalized Thermal Transient Impedance, Junction-to-Ambient (Schottky)**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?73038](http://www.vishay.com/ppg?73038).

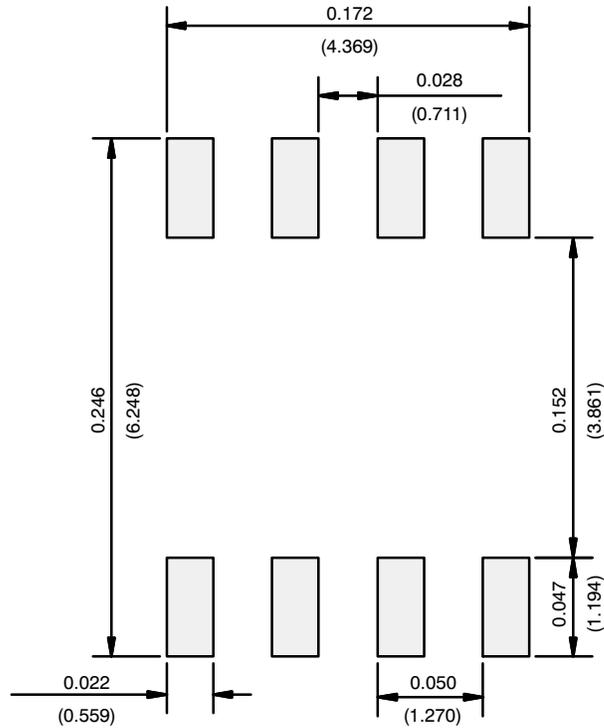
## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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